

# Device level 3D-ICs Through Membrane Projection Lithography Using CMOS Compatible Materials

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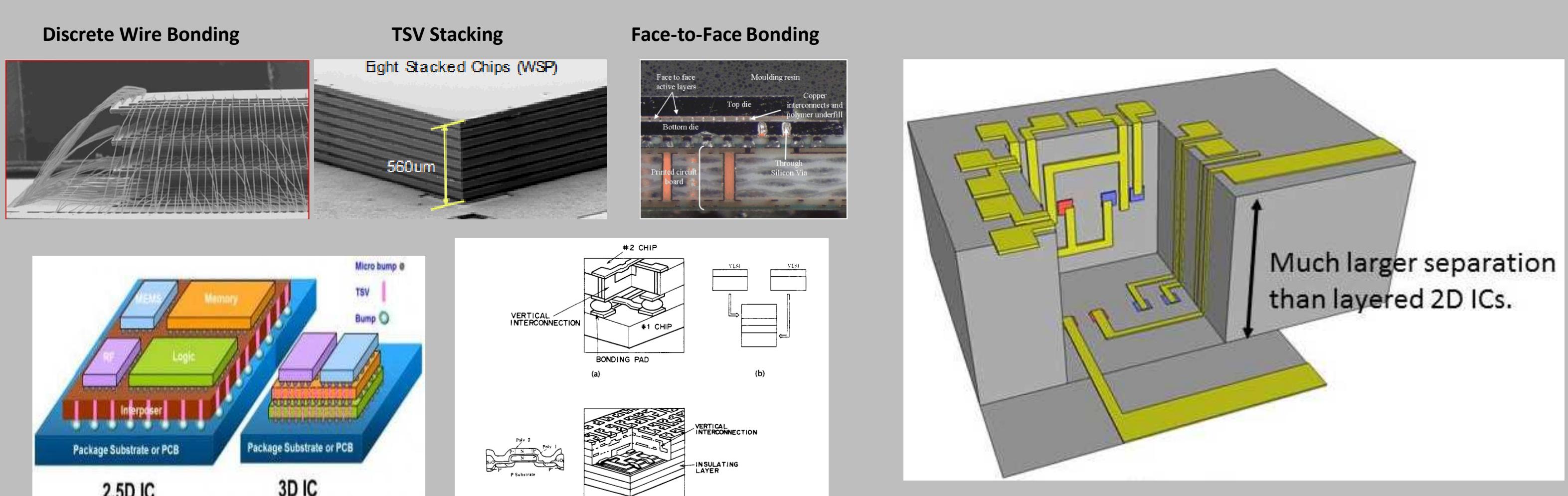


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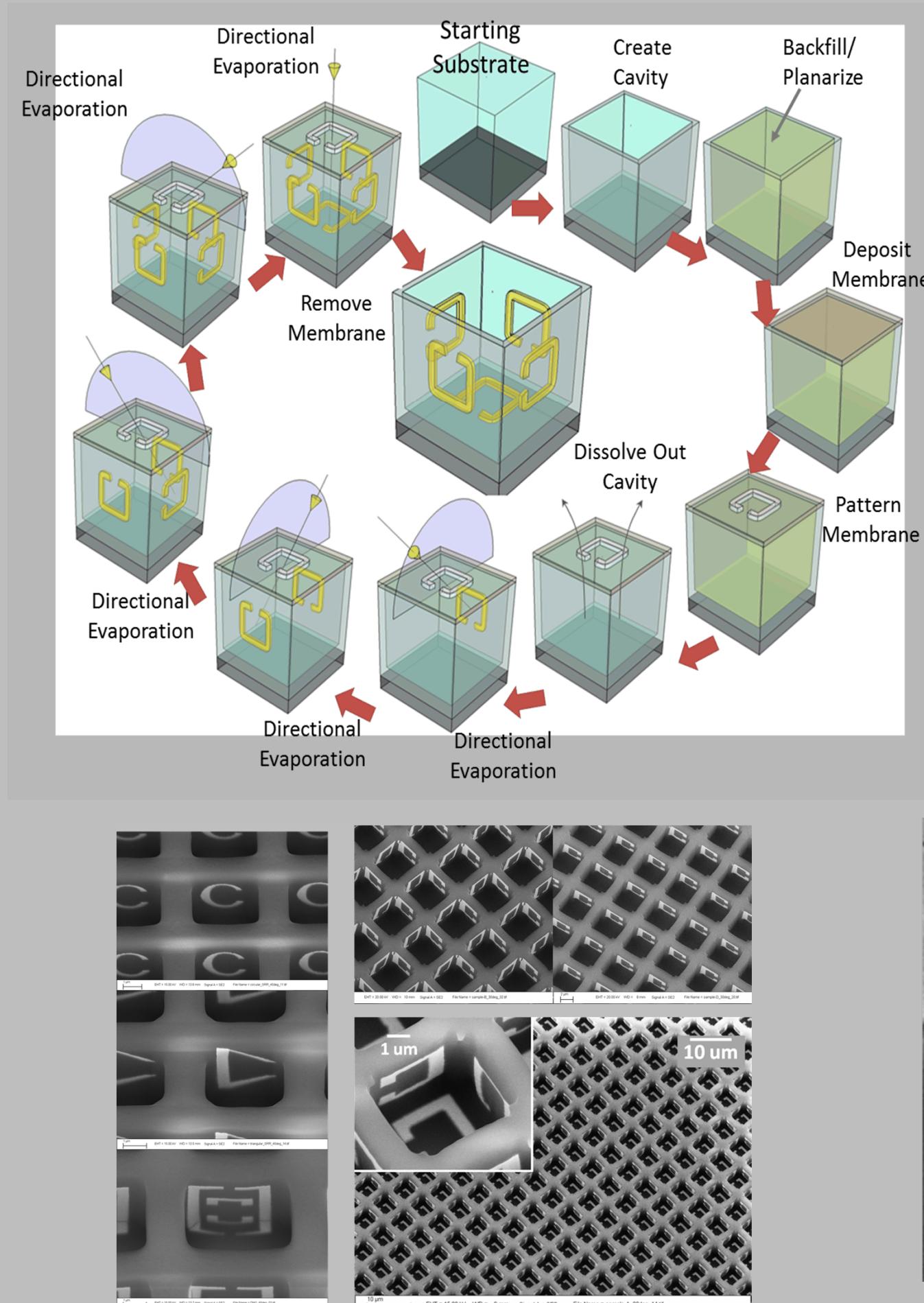
## Oblique Angle Processing

Traditional CMOS fabrication involves a top down vertical approach, with active regions parallel to the wafer surface. Performing standard semiconductor operations at an angle to the wafer surface results in three-dimensional structures with active regions fabricated in any axis relative to the wafer surface.

## Traditional vs. MPL



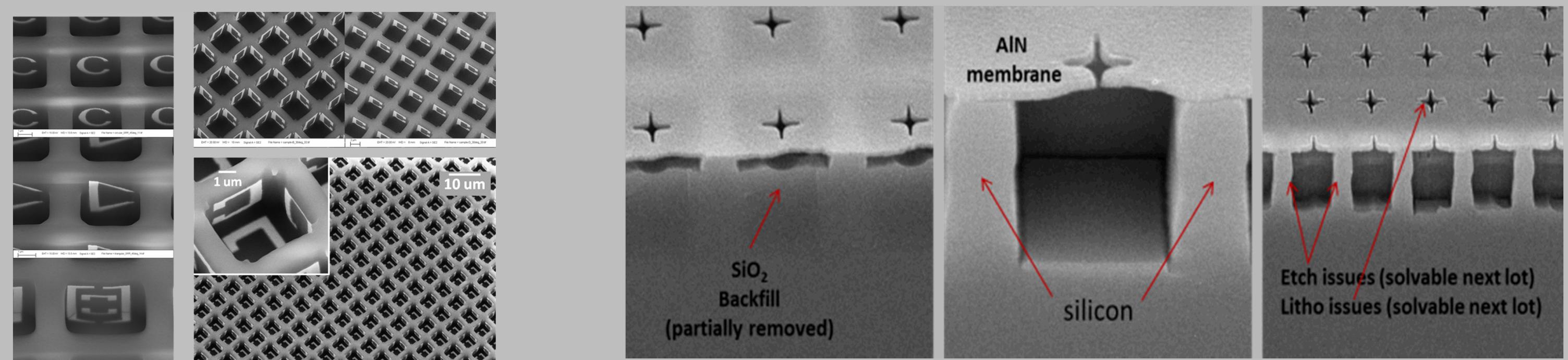
## MPL- Fabrication



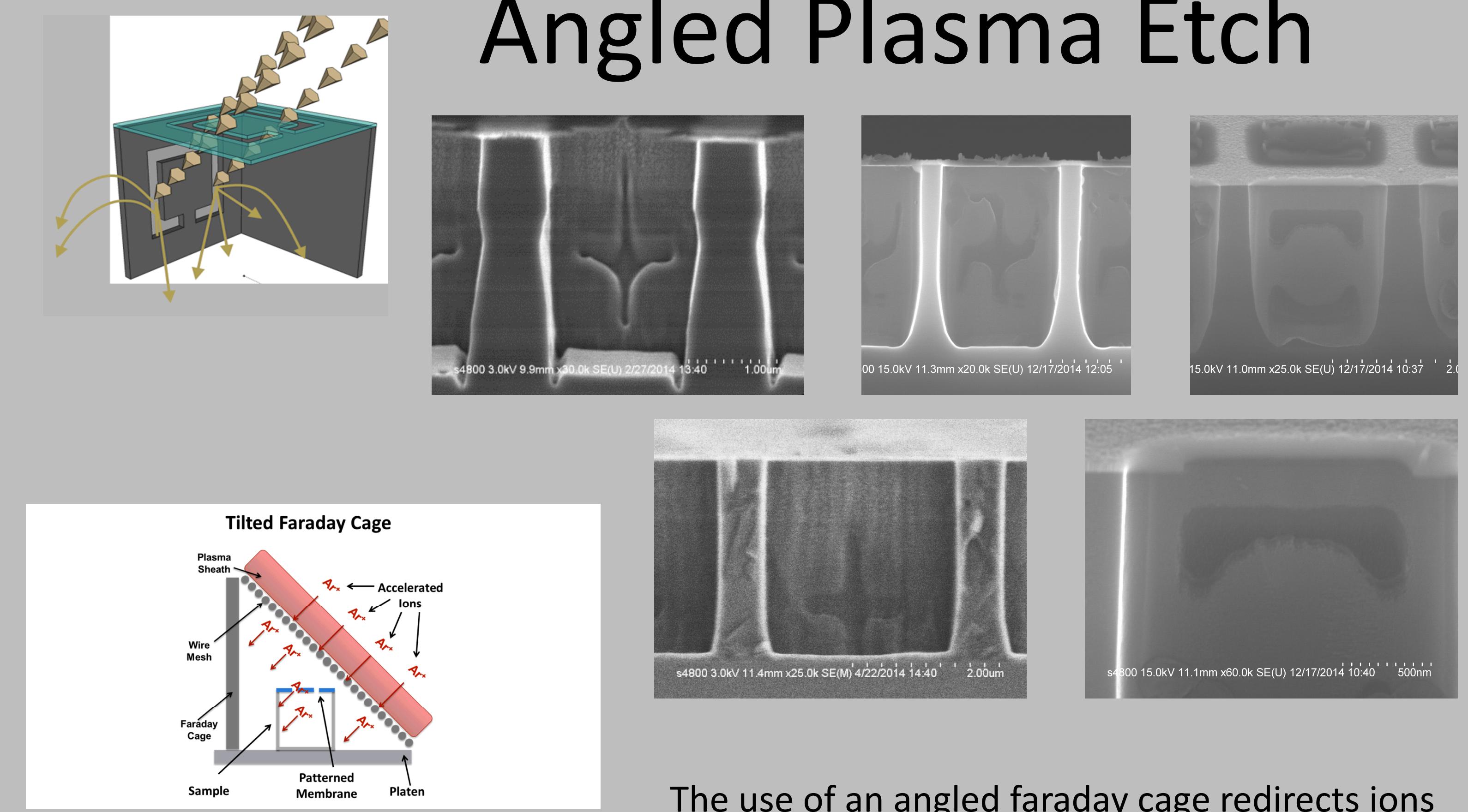
Membrane projection lithography (MPL) is used to create 3-dimensional unit cells in a silicon matrix. Processes can be projected obliquely through a suspended membrane to achieve specific patterns with a wide range of materials.

- Plasma Etch
- Ion Implant
- Physical vapor Deposition

### Material Identification

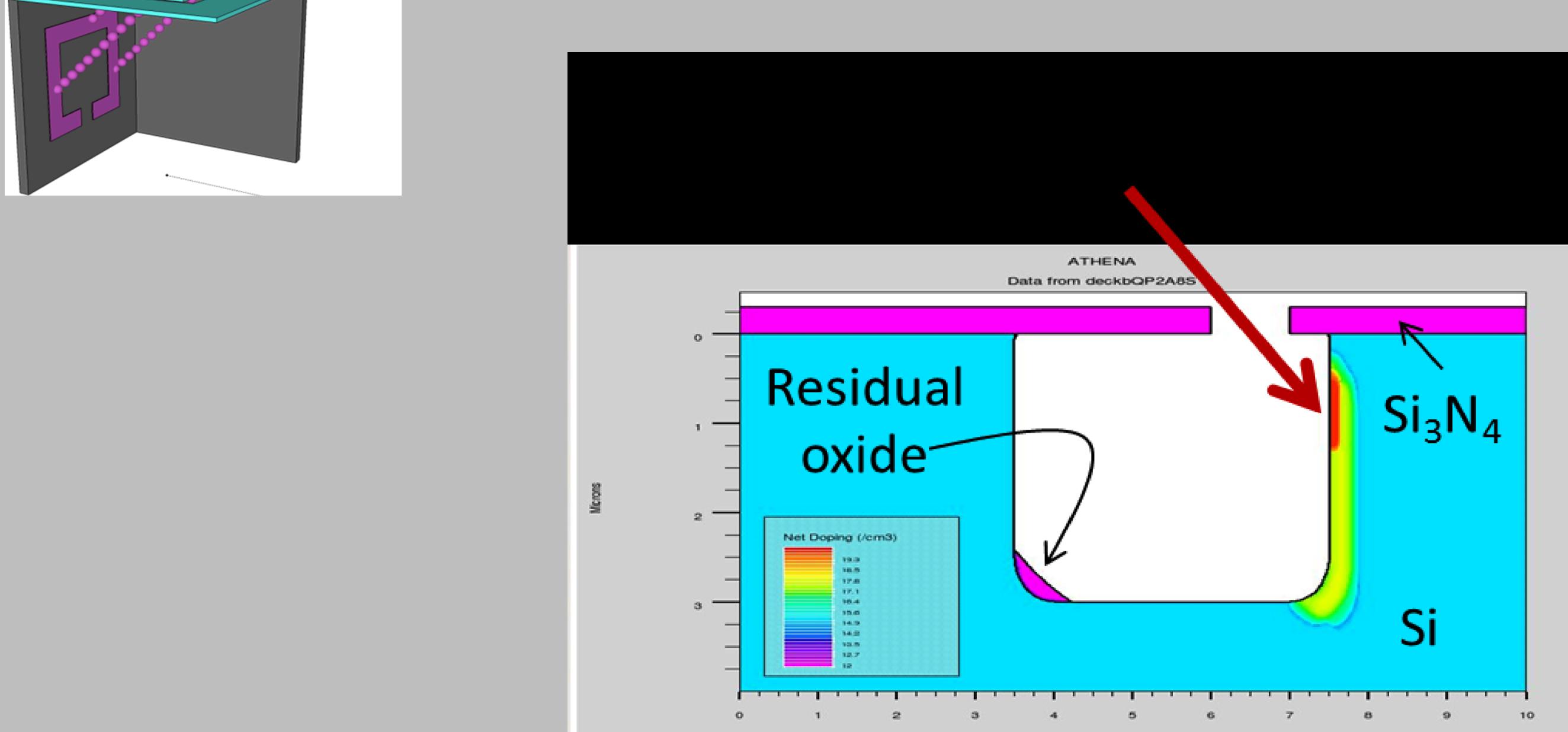


## Angled Plasma Etch



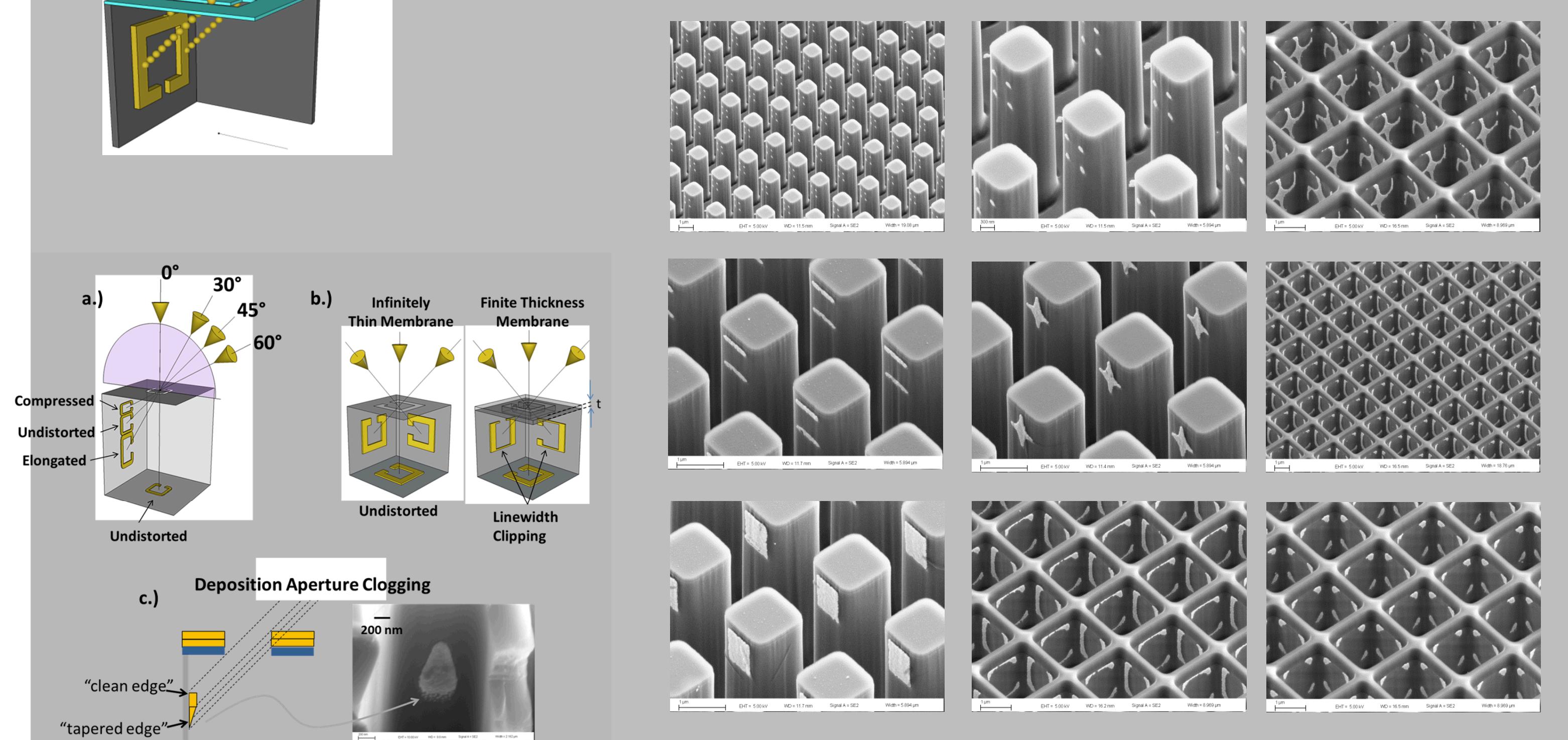
The use of an angled faraday cage redirects ions

## Patterned Ion Implant



Results of 2D process simulation demonstrating feasibility of MPL-based angled implant through a thin suspended membrane.

## Angled deposition



## Future Work

